

L Number	Hits	Search Text	DB	Time stamp
1	12908	(floating adj gate) and (control adj gate)	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/18 13:51
2	5441	((floating adj gate) and (control adj gate)) and (non adj volatile)	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/18 13:51
3	4438	((((floating adj gate) and (control adj gate)) and (non adj volatile)) and source	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/18 13:52
4	610	(((((floating adj gate) and (control adj gate)) and (non adj volatile)) and source) and (select adj transistor)	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/18 13:52
5	505	(((((floating adj gate) and (control adj gate)) and (non adj volatile)) and source) and (select adj transistor)) and well	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/18 13:52
6	52	((((((floating adj gate) and (control adj gate)) and (non adj volatile)) and source) and (select adj transistor)) and well) and (common adj control)	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/18 13:59
7	35	((((((floating adj gate) and (control adj gate)) and (non adj volatile)) and source) and (select adj transistor)) and (365/185.05.ccls.)	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/18 14:04
8	0	((((((floating adj gate) and (control adj gate)) and (non adj volatile)) and source) and (single adj control adj plate)	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/18 14:05
9	199	((((((floating adj gate) and (control adj gate)) and (non adj volatile)) and source) and (select adj transistor)) and (common adj source)	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/18 14:05
10	0	((((((floating adj gate) and (control adj gate)) and (non adj volatile)) and source) and (select adj transistor)) and (common adj source)) and (control adj plate)	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/18 14:06
11	43	((((((floating adj gate) and (control adj gate)) and (non adj volatile)) and source) and (select adj transistor)) and (common adj source)) and (active adj region)	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/18 14:14
12	36	((((((floating adj gate) and (control adj gate)) and (non adj volatile)) and source) and (select adj transistor)) and well) and (selection adj transistor)	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/18 14:16

L Number	Hits	Search Text	DB	Time stamp
1	973	(non adj volatile) and (select adj transistor)	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/20 12:26
2	662	((non adj volatile) and (select adj transistor)) and well	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/20 12:26
3	549	((((non adj volatile) and (select adj transistor)) and well) and substrate	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/20 12:26
4	143	(((((non adj volatile) and (select adj transistor)) and well) and substrate) and biasing	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/20 12:27
5	101	(((((non adj volatile) and (select adj transistor)) and well) and substrate) and biasing) and (word adj line)	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/20 12:27
6	68	(((((non adj volatile) and (select adj transistor)) and well) and substrate) and biasing) and (word adj line)) and block	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/20 12:35
7	106	(((((non adj volatile) and (select adj transistor)) and well) and substrate) and (365/185.18.ccls.)	USPAT; EPO; JPO; DERWENT; USOCR	2003/08/20 12:35